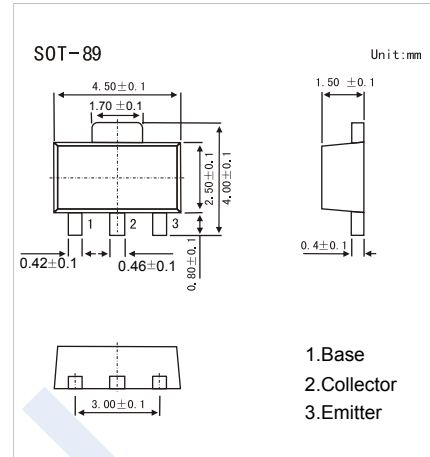


## NPN Transistors

### 2SC2881

#### ■ Features

- Small Flat Package
- High Transition Frequency
- High Voltage
- Complementary to 2SA1201



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CB0</sub>	120	V
Collector - Emitter Voltage	V <sub>CEO</sub>	120	
Emitter - Base Voltage	V <sub>EBO</sub>	5	
Collector Current - Continuous	I <sub>C</sub>	800	mA
Base Current	I <sub>B</sub>	160	
Collector Power Dissipation	P <sub>C</sub>	500	mW
Thermal Resistance From Junction To Ambient	R <sub>θJA</sub>	250	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to 150	

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V <sub>CB0</sub>	I <sub>C</sub> = 100uA, I <sub>E</sub> = 0	120			V
Collector- emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	120			
Emitter - base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = 100uA, I <sub>C</sub> = 0	5			
Collector-base cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 120V, I <sub>E</sub> = 0			0.1	uA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> =0			0.1	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =500 mA, I <sub>B</sub> =50mA			1	V
Base - emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =500 mA, I <sub>B</sub> =50mA			1.2	
Base - emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = 5V, I <sub>C</sub> = 0.5A			1	
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 5V, I <sub>C</sub> = 100mA	80		240	
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f=1MHz			30	pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 5V, I <sub>C</sub> = 100mA		120		MHz

#### ■ Classification of h<sub>FE</sub>

Marking	CO*	CY*
Rank	O	Y
Range	80-160	120-240

# NPN Transistors

## 2SC2881

### Typical Characteristics

